



30V P-Channel Trench Power MOSFET

General Description

The SJJ30P030 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a wide variety of applications.

Features

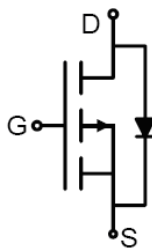
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handling capability
- Lead free product is acquired

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

Key Performance Parameters

Parameter	Value	Unit
V_{DS}	-30	V
$R_{DS(ON_TYP)}$	3.3	m Ω
I_D	-129	A
Q_G	130	nC



Schematic Diagram



TO-263 top view



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJJ30P030	SJJ30P030	TO-263	Tape	\	\	1000 Pcs

Table 1. Absolute Maximum Ratings ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0\text{V}$)	-30	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0\text{V}$)	± 20	V
I_D	Drain Current-Continuous($T_C=25^{\circ}\text{C}$)	-129	A
	Drain Current-Continuous($T_C=100^{\circ}\text{C}$)	-81	A
$I_{DM}(\text{pluse})$	Drain Current-Continuous@ Current-Pulsed (Note 1)	-516	A
P_D	Maximum Power Dissipation($T_C=25^{\circ}\text{C}$)	114	W
	Maximum Power Dissipation($T_C=100^{\circ}\text{C}$)	45	W
E_{AS}	Avalanche energy (Note 2)	576	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.1	$^{\circ}\text{C}/\text{W}$



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Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V T _J =25℃			-1	μA
		V _{DS} =-30V, V _{GS} =0V T _J =125℃			-100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.7	-2.5	V
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-20A		63		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-20A		3.3	4.3	mΩ
		V _{GS} =-4.5V, I _D =-20A		5.1	6.8	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1.0MHz		7000		pF
C _{oss}	Output Capacitance			820		pF
C _{rss}	Reverse Transfer Capacitance			540		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		2.2		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =-10V, V _{DS} =-15V, R _L =0.75Ω, R _{GEN} =3Ω		13		nS
t _r	Turn-on Rise Time			32		nS
t _{d(off)}	Turn-Off Delay Time			27		nS
t _f	Turn-Off Fall Time			9		nS
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-20A		130		nC
Q _{gs}	Gate-Source Charge			12		nC
Q _{gd}	Gate-Drain Charge			31		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				-129	A
V _{SD}	Forward on Voltage ^(Note 3)	V _{GS} =0V, I _S =-20A			-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-20A, di/dt=-100A/μs		30		ns
Q _{rr}	Reverse Recovery Charge	I _F =-20A, di/dt=-100A/μs		40		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

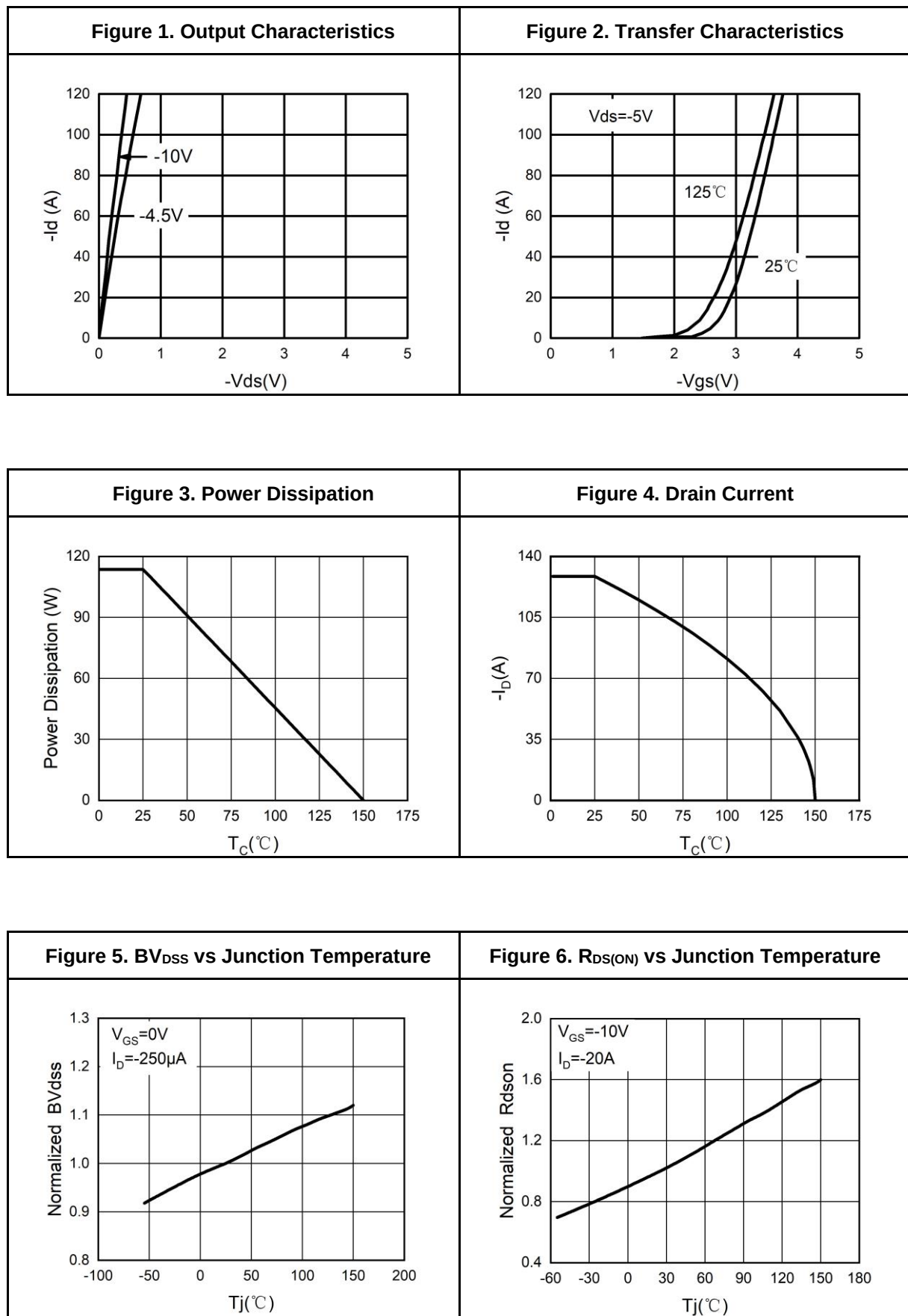
Notes 2.EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=-30V, V_G=-10V, R_g=25\Omega, L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



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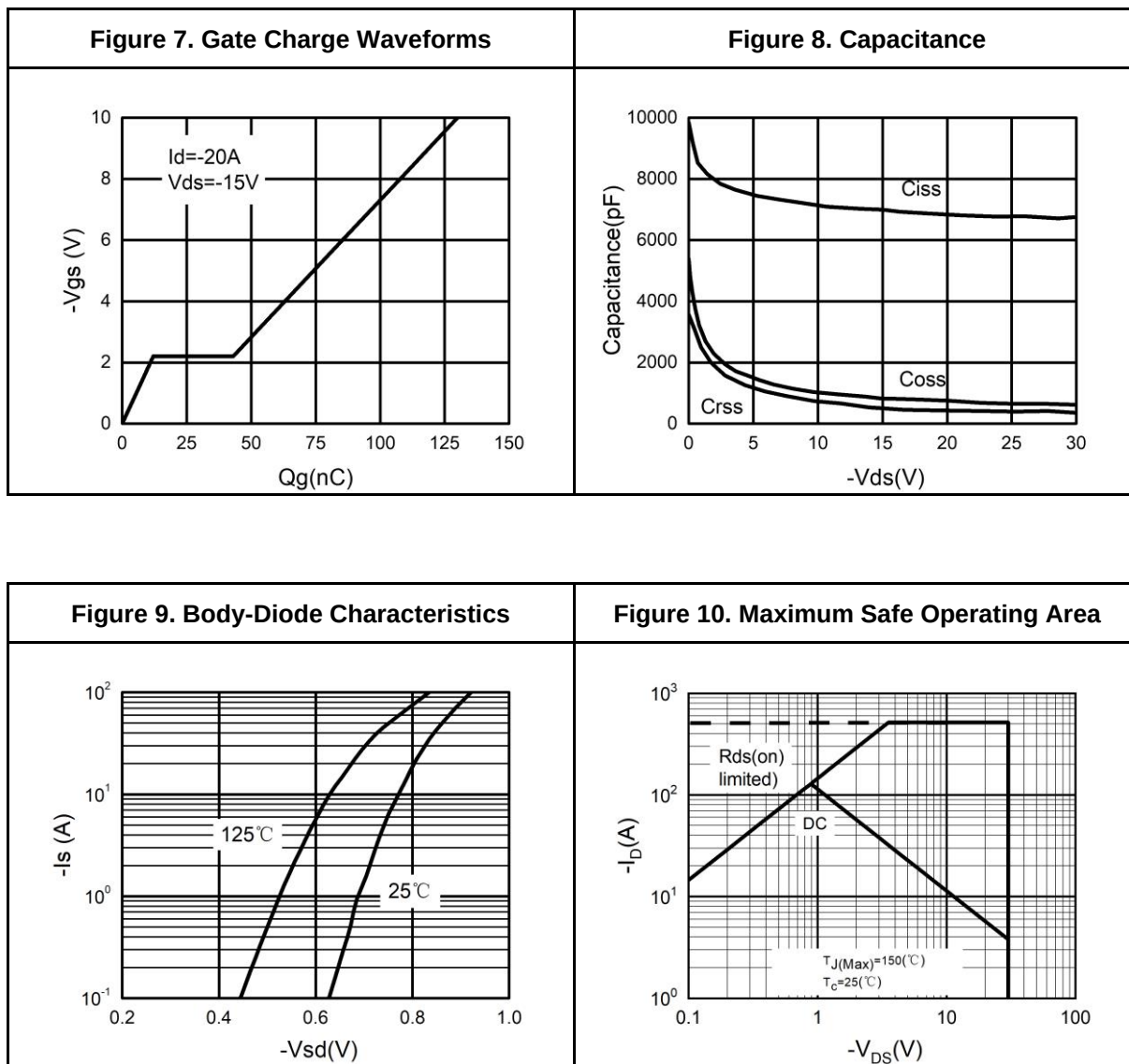
Typical Electrical And Thermal Characteristics (Curves)





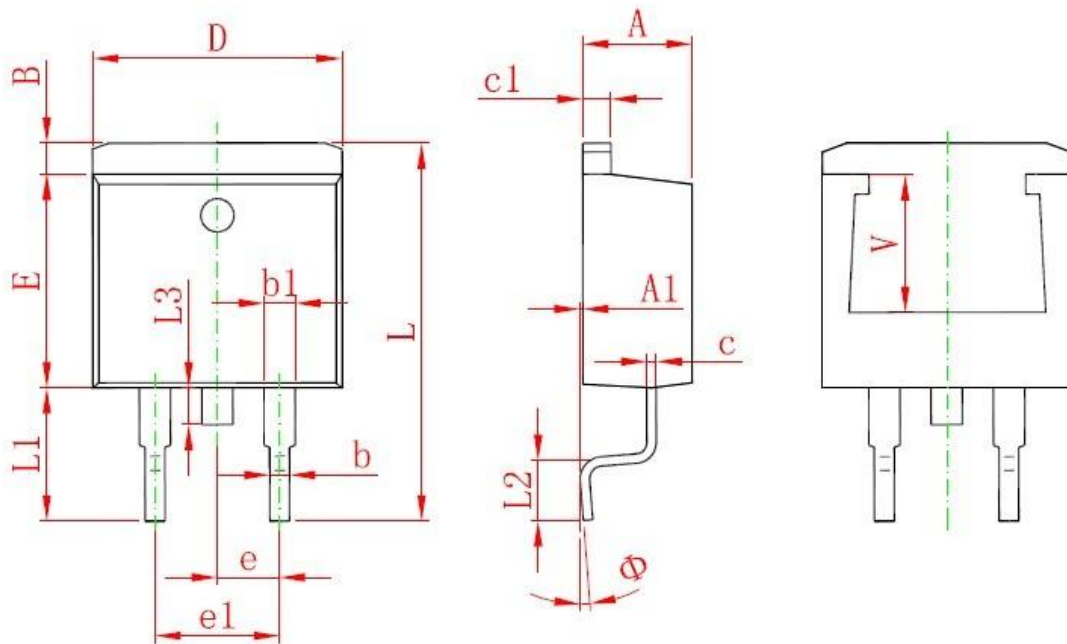
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Typical Electrical And Thermal Characteristics (Curves)





TO-263 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Ma
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF.		0.220REF.	
Φ	0°	8°	0°	8°



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